

CLEAN VERSION OF THE AMENDMENT

IN THE SPECIFICATION

ay The present application is a continuation of co-pending U.S. Patent Application Serial No. 09/563,030, filed May 1, 2000, which is a continuation of U.S. Patent Application Serial No. 09/132,876, filed August 11, 1998, now U.S. Patent No. 6,077,784, which claims priority from Taiwan Application No. 87110514, filed June 30, 1998, all the disclosures of which are herein specifically incorporated by this reference.

IN THE CLAIMS

22 28. (New) A chemical-mechanical polishing process, comprising the steps of:

forming a first conductive layer and a dielectric layer over a semiconductor substrate;

polishing the dielectric layer to form a substantially planar surface; and forming a dielectric cap layer over the dielectric layer.

29. (New) The process of claim 28, wherein the step of forming the conductive layer includes depositing doped polysilicon.

30. (New) The process of claim 28, wherein the step of forming the dielectric layer includes a high-density plasma chemical vapor deposition method.

31. (New) The process of claim 28, wherein the step of forming the dielectric layer includes depositing silicon dioxide.

32. (New) The process of claim 28, wherein the step of forming the dielectric layer includes depositing silicon dioxide.

33. (New) The process of claim 28, wherein the step of forming the cap layer includes depositing a silicon oxide layer using a plasma-enhanced chemical vapor deposition method with silane (SiH₄) as the main reactive agent.